Ref	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	715	plasma with dop\$3 with (silicon or polysilicon or HSG) with (phosphorus or phosphine or PH3 or "PH3" or "PH.sub.3" or "P H.sub. 3")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/30 16:18
L2	0	chamber with plasma with dop\$3 with (silicon or polysilicon or HSG) with (phosphorus or phosphine or PH3 or "PH3" or "PH.sub.3" or "P H. sub.3") with temperature with pressure with power	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/30 15:33
L3	0	plasma with dop\$3 with (silicon or polysilicon or HSG) with (phosphorus or phosphine or PH3 or "PH3" or "PH.sub.3" or "P H.sub. 3") with temperature with pressure with power	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/30 15:33
L4	831770	capacitor or capacitors or DRAM or DRAMs or (dynamic adj random adj access adj (memory or memories))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/30 15:33
L5	9	1 same chamber same temperature same pressure same power	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/30 15:34
L6	230	(plasma near2 dop\$3) with (silicon or polysilicon or HSG) with (phosphorus or phosphine or PH3 or "PH3" or "PH.sub.3" or "P H.sub. 3")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/30 17:58
L7	1	("20040203201").PN.	US-PGPUB; USPAT	OR	OFF	2006/04/30 18:36
L8	1	("6218260").PN.	US-PGPUB; USPAT	OR	OFF	2006/04/30 18:36
S1	7561	doped near5 (amorphous adj silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 17:22

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S2	1386	undoped near5 (amorphous adj silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 16:36
S3	627	S1 with S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 16:36
S4	831409	capacitor or capacitors or DRAM or DRAMs or (dynamic adj random adj access adj (memory or memories))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/30 15:33
S5	278	S3 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 17:19
S6	242	S5 and @ad <= "20031230"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 16:39
S7	27	suppress\$4 with dopant\$1 with agglomerat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	OFF	2006/04/29 16:43
S8	11339	mps or "mps" or (metastable-polysilicon) or meta-stable-polysilicon or (meta adj stable adj polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 16:46
S9	9	S5 and S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 16:46

S10	9128	plasma near15 dop\$3	US-PGPUB; USPAT; USOCR;	OR	OFF	2006/04/30 15:30
			EPO; JPO; DERWENT; IBM_TDB			
S11	67358	insitu or in-situ or (in adj situ)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 16:53
S12	23	S1 with S2 with S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 16:56
S13	5	S5 and S10 and S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 16:56
S14	23	S1 with S2 with S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 17:19
S15	4656	HSG\$1 or (hemispher\$6 near3 (grain\$1 or silicon or polysilicon))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 17:22
S16	62840	amorphous adj silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 17:22
S17	752	S15 with S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 17:22

S18	681	S17 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 17:23
S19	81	S18 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/29 17:49
S20	1	("20010030336").PN.	US-PGPUB; USPAT	OR	OFF	2006/04/29 17:50
S21	0	S20 and S11	US-PGPUB; USPAT	OR	OFF	2006/04/29 17:50